Form 1449* Atty. Docket No.: 303.444US5 INFORMATION DISCLOSURE STATEMENT Applicant: Scott G. Meikle et al. BY APPLICANT (Use several sheets if necessary) Filing Date: Herewith U.S. PATENT DOCUMENTS

Serial No. Unknown

Group: Unknow

**Examiner							
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^{**}EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 2 of 2

Form	1449*

Atty. Docket No.: 303.444US5

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INFORMATION DISCLOSURE STATEMENT
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Applicant: Scott G. Meikle et al.

Filing Date: Herewith

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